# Test Procedure for the NCV7420GEVB

**ON Semiconductor®** 



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# **Required Equipment**

- Oscilloscope
- Bench Power Supply
- Voltmeter
- Signal Generator



Figure 1: Test Setup Configuration

### Test procedure Step 1 (Power-up sequence, Standby mode):

- 1. Connect the setup as shown above.
- 2. Set STB, EN and TxD and G (LIN Switch Gate) to LOW.
- 3. Apply an input voltage,  $V_{BAT} = 12 V$
- 4. Set STB and TxD to HIGH
- 5. Check V<sub>CC</sub>, LIN, INH and RxD State
- 6. Check I<sub>BAT</sub>. Caution should be taken with oscilloscope digital probes resistance which could have influence on overall I<sub>BAT</sub> current.

#### Table 1: Desired Results

$I_{BAT}$ = Typ. 40 µA, Max. 60 µA (Measured with disconnected digital probes), no V <sub>CC</sub> Load)
$V_{CC} = ON$
LIN = RECESSIVE
INH = FLOATING
RxD = HIGH

### **Test procedure Step 2 (Transition to Normal mode):**

- 1. Set EN HIGH
- 2. Check V<sub>CC</sub>, LIN, INH and RxD State
- 3. Check I<sub>BAT</sub>. Caution should be taken with oscilloscope digital probes resistance which could have influence on overall I<sub>BAT</sub> current.

#### **Table 2: Desired Results**

$I_{BAT}$ = Typ. 0.64 mA, Max 1 mA (Measured with disconnected digital probes, no V <sub>CC</sub> Load)
$V_{CC} = ON$
LIN = RECESSIVE
INH = ON
RxD = HIGH

# Test procedure Step 3 (Transmit in Normal mode):

- 1. Set TxD to LOW, wait <6ms, set TxD HIGH (Generate LIN Dominant state)
- 2. Observe LIN and RxD. Start observation with TxD falling edge.

### **Table 3: Desired Results**

LIN = Contain one Dominant pattern
RxD = Contain one Dominant pattern

## **Test procedure Step 4 (Transition to Sleep mode):**

- 1. Set STB to LOW
- 2. Set EN LOW
- 3. Set TxD LOW (to simulate a microcontroller without power supply being connected to TxD)
- 4. Check I<sub>BAT</sub>, V<sub>CC</sub>, INH and RxD State

#### Table 4: Desired Results

$I_{BAT} = Typ. 11 \ \mu A, Max 20 \ \mu A$
$V_{\rm CC} = \rm OFF$
INH = FLOATING
RxD = LOW

## **Test procedure Step 5 (Local Wakeup):**

- 1. In Sleep, press Local Wakeup switch
- 2. Set STB and TxD to HIGH
- 3. Check V<sub>CC</sub>, INH and RxD State
- 4. Check  $I_{BAT}$ . Caution should be taken with oscilloscope digital probes resistance which could have influence on overall  $I_{BAT}$  current.

#### Table 5: Desired Results

$I_{BAT}$ = Typ. 40 µA, Max. 60 µA (Measured with disconnected digital probes), no V <sub>CC</sub> Load)
$V_{CC} = ON$
INH = FLOATING
RxD = HIGH – Signaling Wakeup source – Local Wakeup

### **Test procedure Step 6 (Remote Wakeup):**

- 1. In Sleep, generate Remote Wakeup pattern: Set G HIGH, wait >150 us, set G LOW
- 2. Set STB and TxD to HIGH
- 3. Check V<sub>CC</sub>, INH and RxD State
- 4. Check I<sub>BAT</sub>. Caution should be taken with oscilloscope digital probes resistance which could have influence on overall I<sub>BAT</sub> current.

#### Table 6: Desired Results

$I_{BAT} = Typ. 0.37 \text{ mA} - 3.3 \text{V}$ version
$I_{BAT} = Typ. 0.56 \text{ mA} - 5V \text{ version}$
(RxD 10 k $\Omega$ pull-up to V <sub>CC</sub> + 40 $\mu$ A Standby current consumption)
(Measured with disconnected digital probes), no V <sub>CC</sub> Load)
$V_{CC} = ON$
INH = FLOATING
RxD = LOW – Signaling Wakeup source – Remote Wakeup

	MIN	ТҮР	MAX
LIN DOMINANT			2 V
LIN RECESSIVE	V <sub>BAT</sub> - 1 V		
INH HIGH	V <sub>BAT</sub> - 0.75 V		
VCC ON (3.3 V version)	3.19 V	3.3 V	3.41 V
VCC ON (5 V version)	4.83 V	5.0 V	5.17 V
RxD LOW			0.65 V
RxD HIGH	V <sub>CC</sub> -0.65 V		

## **DC Characteristics**